

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_D \max$ $T_A = +25^\circ\text{C}$
-60V	25m $\Omega$ @ $V_{GS} = -10\text{V}$	-7.7A
	33m $\Omega$ @ $V_{GS} = -4.5\text{V}$	-6.8A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

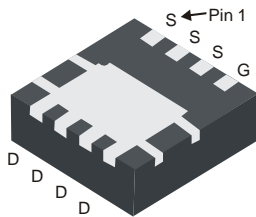
## Features and Benefits

- Low  $R_{DS(ON)}$  – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

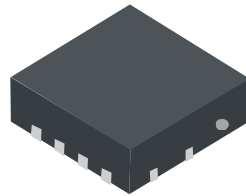
## Mechanical Data

- Case: POWERDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (Approximate)

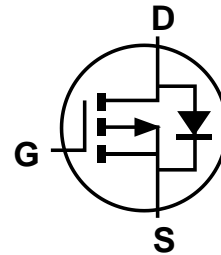
POWERDI<sup>®</sup>3333-8



Bottom View



Top View



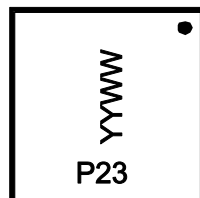
Equivalent Circuit

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMP6023LFGQ-7	POWERDI <sup>®</sup> 3333-8	2,000/Tape & Reel
DMP6023LFGQ-13	POWERDI <sup>®</sup> 3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html)
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



P23 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 13 = 2013)  
 WW = Week Code (01 ~ 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	-60	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C	-7.7	A
		T <sub>A</sub> = +70°C	-6.2	A
	t < 10s	T <sub>A</sub> = +25°C	-10.3	A
		T <sub>A</sub> = +70°C	-8.2	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-55	A	
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	-2.2	A	
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	-35.5	A	
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	62.9	mJ	

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)	P <sub>D</sub>	1.0	W	
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	Steady State	123	°C/W
		t < 10s	69	
Total Power Dissipation (Note 7)	P <sub>D</sub>	2.1	W	
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	Steady State	60	°C/W
		t < 10s	34	
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	6.3	°C	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	—	-3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	25	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A
		—	—	33		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>ISS</sub>	—	2569	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>OSS</sub>	—	179	—	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	143	—	pF	
Gate Resistance	R <sub>g</sub>	—	8	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	26.5	—	nC	V <sub>DS</sub> = -30V, I <sub>D</sub> = -5A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	53.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	7.1	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	12.6	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	6	—	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -30V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = -5A
Turn-On Rise Time	t <sub>R</sub>	—	7.1	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	110	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	62	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	20	—	ns	I <sub>F</sub> = -5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	14	—	nC	

- Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to product testing.

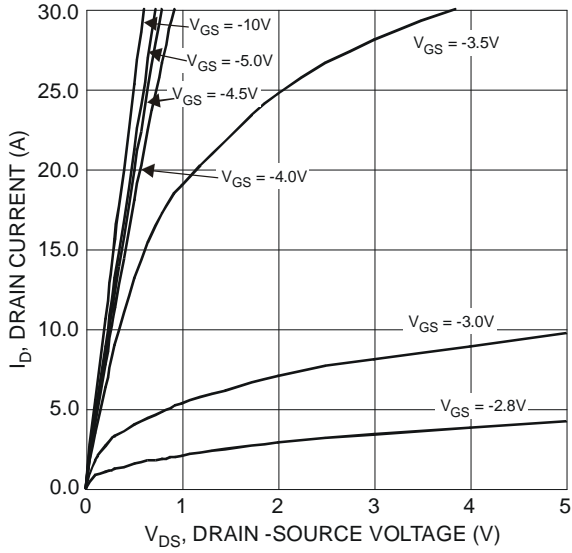


Figure 1 Typical Output Characteristics

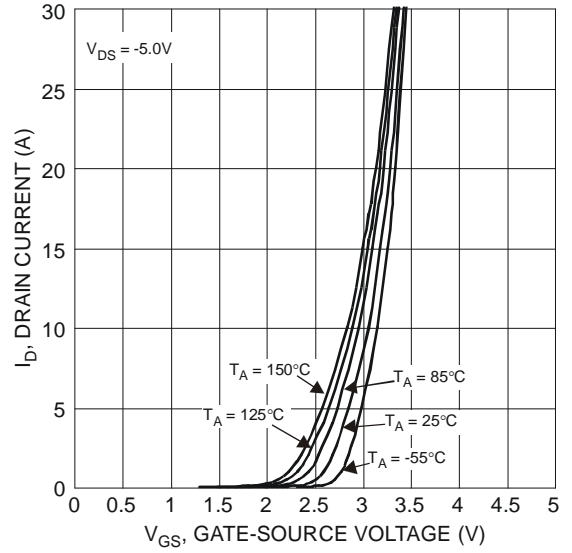


Figure 2 Typical Transfer Characteristics

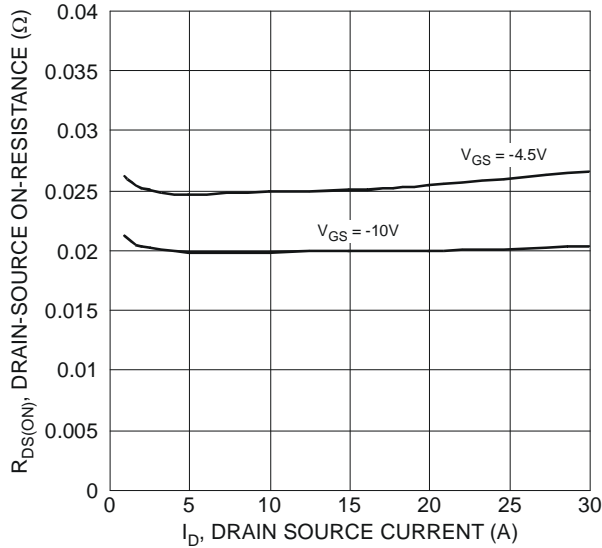


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

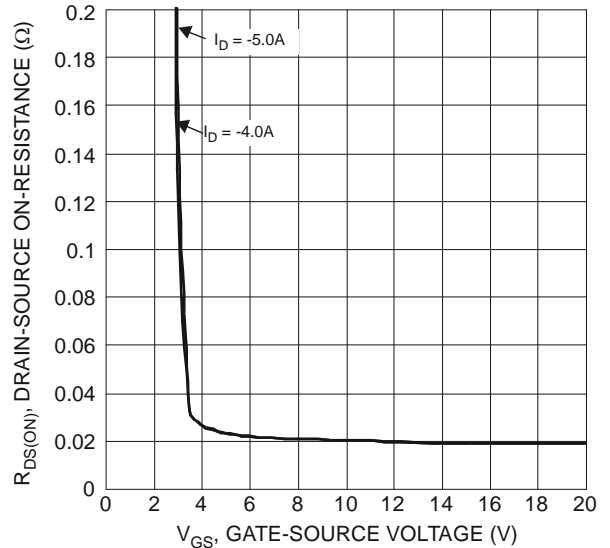


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

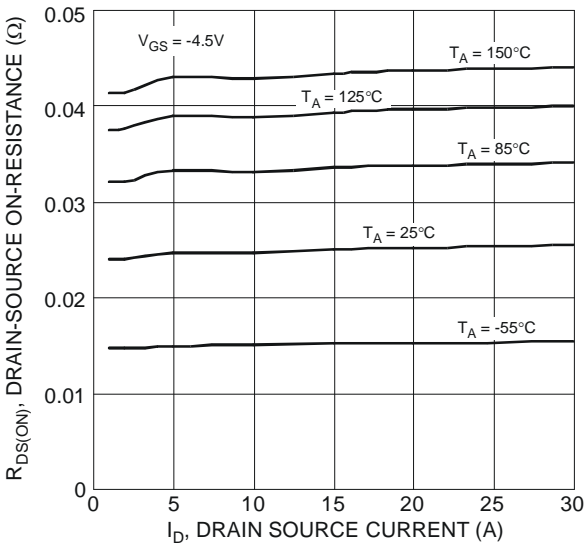


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

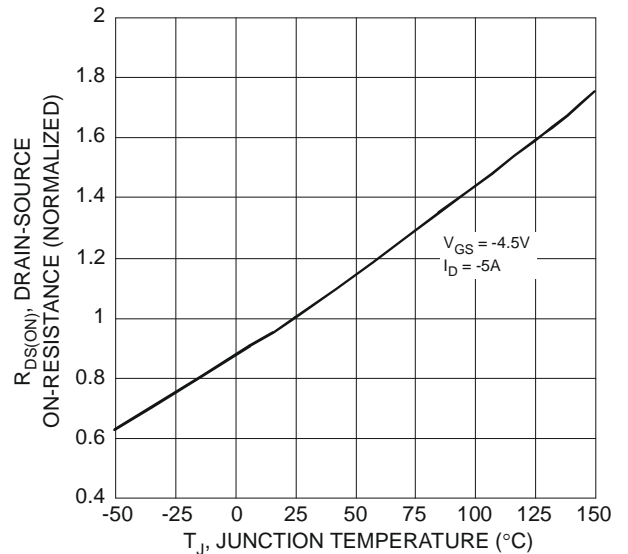


Figure 6 On-Resistance Variation with Temperature

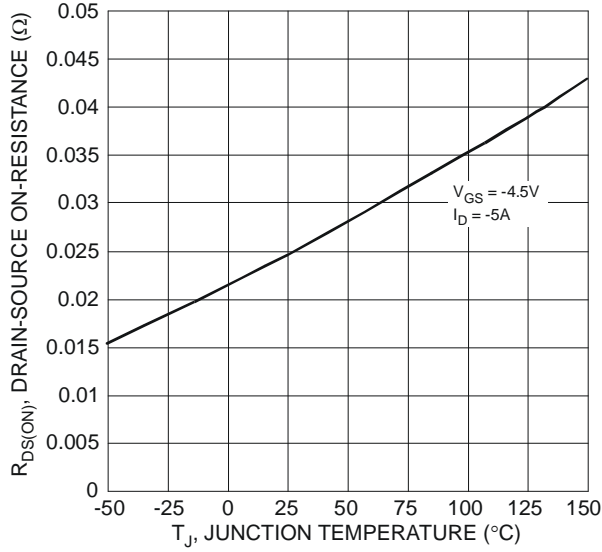


Figure 7 On-Resistance Variation with Temperature

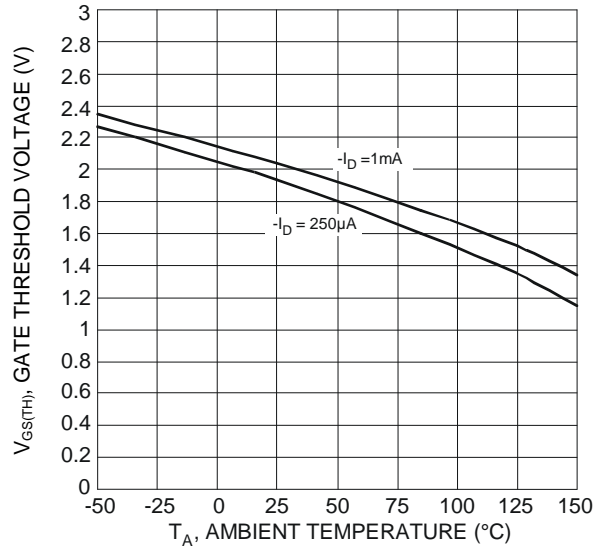


Figure 8 Gate Threshold Variation vs. Ambient Temperature

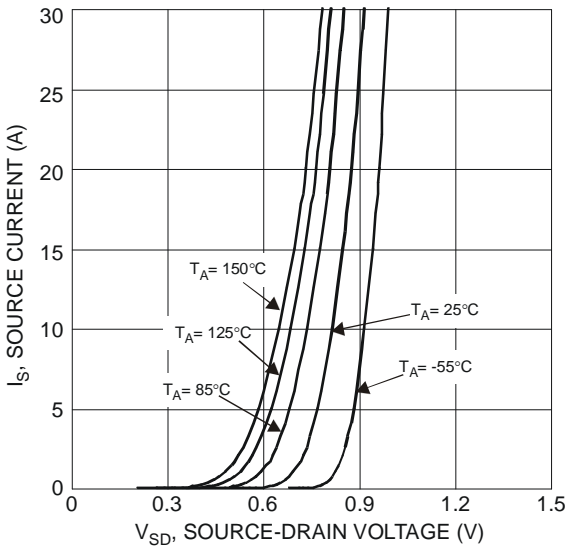


Figure 9 Diode Forward Voltage vs. Current

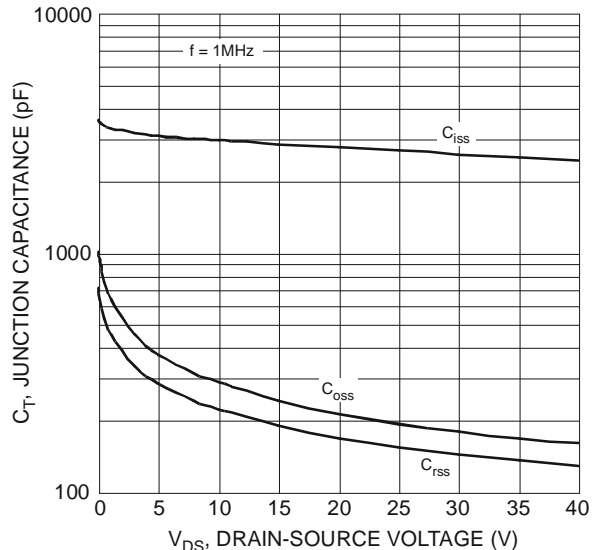


Figure 10 Typical Junction Capacitance

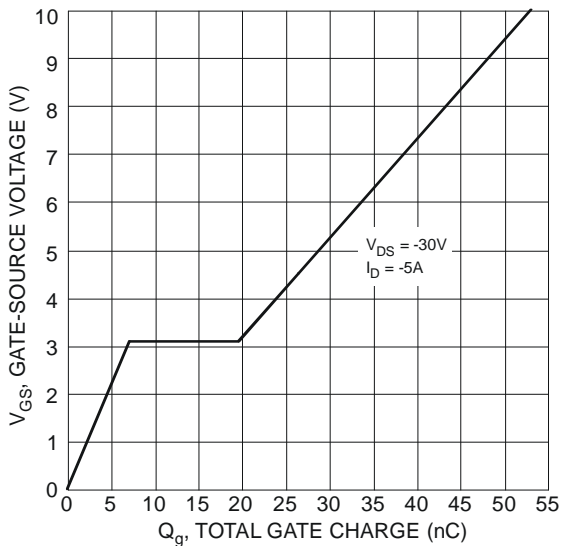


Figure 11 Gate-Charge Characteristics

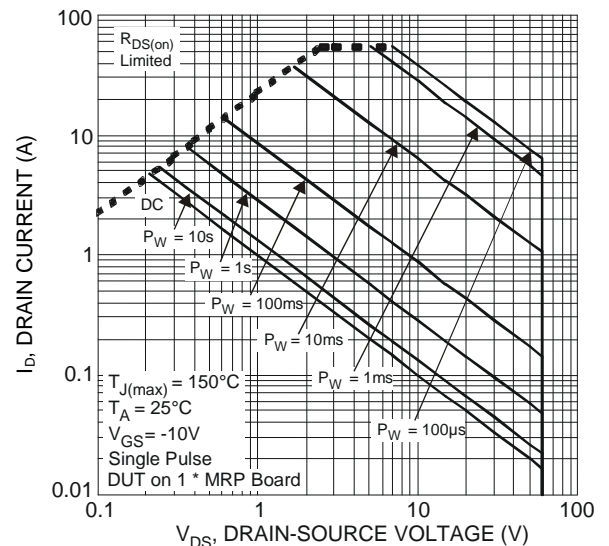
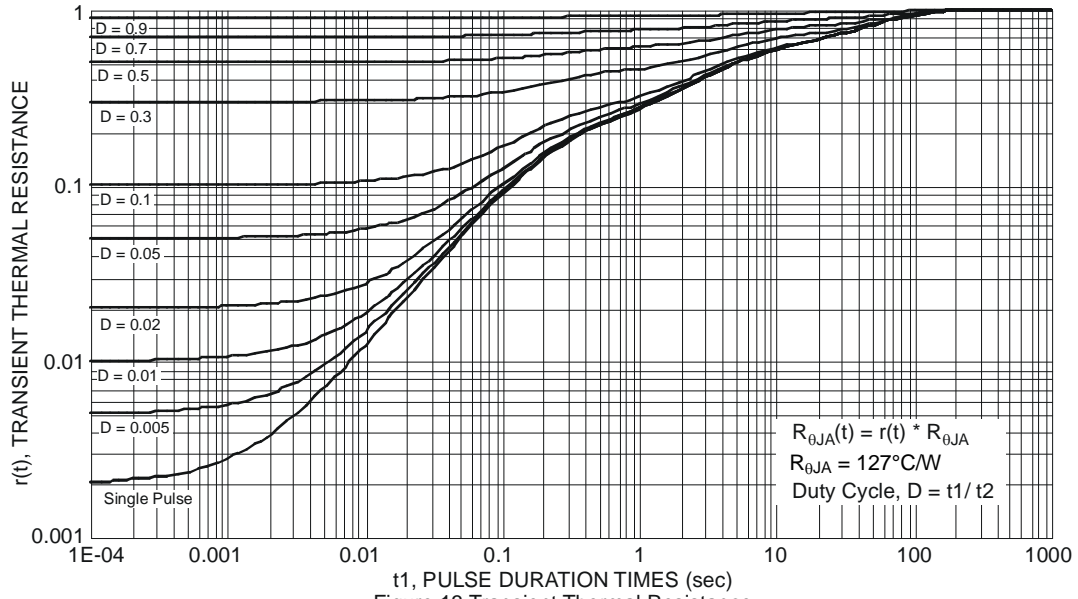


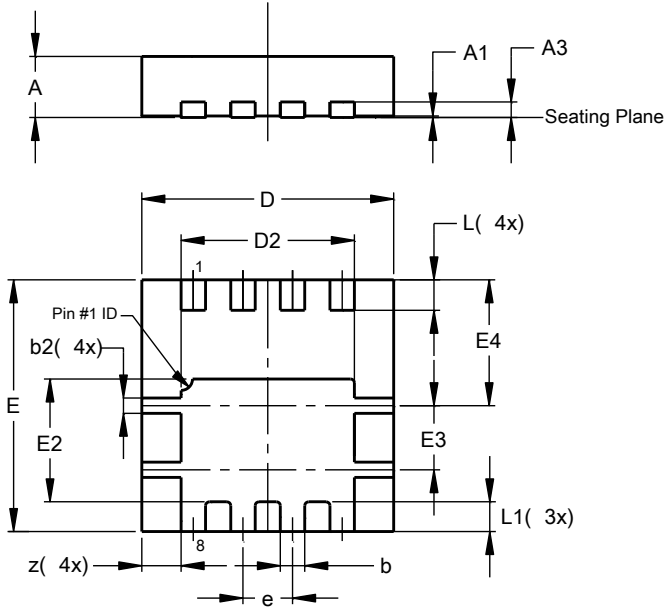
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**POWERDI®3333-8**

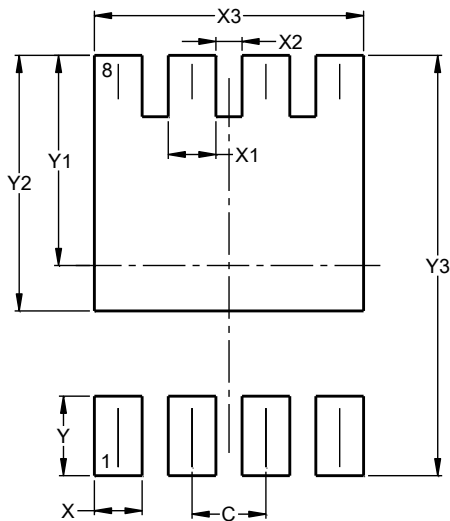


POWERDI®3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**POWERDI®3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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